

ABSTRACT**METHOD FOR PROCESSING A PRECURSOR OF A
HETEROJUNCTION PHOTOVOLTAIC CELL**

One aspect of the invention relates to a method for treating a stack (10'), the stack
5 comprising:

- a substrate (11) of crystalline silicon;
- a first passivation layer (14) of hydrogenated amorphous silicon, disposed
on a first face (11a) of the substrate (11); and
- a first layer (12) of n-doped amorphous silicon, disposed on the first
10 passivation layer (14);

the method comprising a step of exposing the stack (10') to electromagnetic radiation
(20) emitted by an electromagnetic radiation source (40), the first face (11a) of the
substrate (11) pointing to the electromagnetic radiation source (40), the
electromagnetic radiation (20) having at least one first wavelength of between 300 nm
15 and 550 nm and at least one second wavelength of between 550 nm and 1100 nm.

[Fig. to be published with the abstract: Fig. 2]